## 20V PNP LOW SAT MEDIUM POWER TRANSISTOR IN SOT23-6

### SUMMARY

 $BV_{CEO} = -20V : R_{SAT} = 31m\Omega; I_{C} = -3.5A$ 

## DESCRIPTION

Packaged in the SOT23-6 outline this new low saturation 20V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

### FEATURES

- 3.5 Amps continuous current
- Extremely low saturation voltage (-70mV max @ 1A/100mA )
- Up to 10 Amps peak current
- Very low saturation voltages

### **APPLICATIONS**

- DC DC converters
- · Battery charging
- · Power switches
- Motor control
- Power management functions

### **ORDERING INFORMATION**

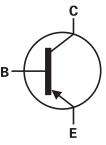
DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXTP2006E6TA	7″	8mm embossed	3,000
ZXTP2006E6TC	13″	8mm embossed	10,000

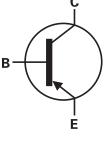
#### **DEVICE MARKING**

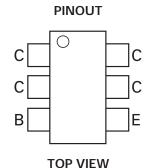
52



SOT23-6







## ABSOLUTE MAXIMUM RATINGS

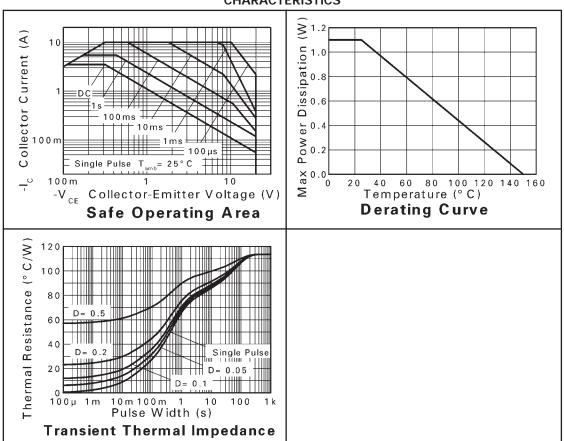
PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	BV <sub>CBO</sub>	-25	V
Collector-emitter voltage	BV <sub>CEO</sub>	-20	V
Emitter-base voltage	BV <sub>EBO</sub>	-7.5	V
Continuous collector current	I <sub>C</sub>	-3.5	A
Peak pulse current	I <sub>CM</sub>	-10	A
Power dissipation at $T_A = 25 \degree C^{(a)}$	PD	1.1	W
Linear derating factor		8.8	mW/°C
Power dissipation at $T_A = 25 \degree C^{(b)}$	P <sub>D</sub>	1.7	W
Linear derating factor		13.6	mW/°C

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	113	°C/W
Junction to ambient <sup>(b)</sup>	R <sub>θJC</sub>	73	°C/W

NOTES

(a) For a device surface mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. (b) As above measured at t<5 seconds.



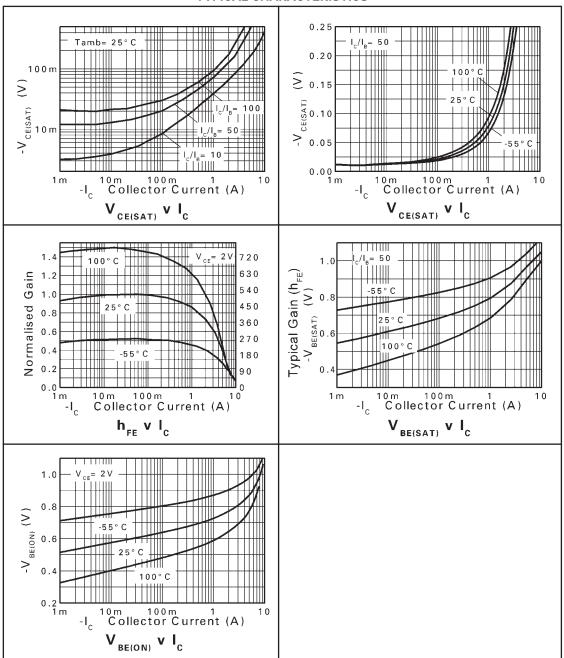
**CHARACTERISTICS** 

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	BV <sub>CBO</sub>	-25	-49		V	I <sub>C</sub> = -100μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	-20	-43		V	I <sub>C</sub> = -10mA *
Emitter-base breakdown voltage	BV <sub>EBO</sub>	-7.5	-8.4		V	I <sub>E</sub> = -100μA
Collector cut-off current	I <sub>CBO</sub>			-100	nA	V <sub>CB</sub> = -20V
Collector cut-off current	I <sub>CES</sub>			-100	nA	V <sub>CB</sub> = -20V
Emitter cut-off current	I <sub>EBO</sub>			-100	nA	$V_{EB} = -6V$
Collector-emitter saturation voltage	V <sub>CE(SAT)</sub>		-10	-15	mV	I <sub>C</sub> = -0.1A, I <sub>B</sub> = -10mA*
			-100	-140	mV	I <sub>C</sub> = -1A, I <sub>B</sub> = -10mA*
			-110	-130	mV	I <sub>C</sub> = -3.5A, I <sub>B</sub> = -350mA*
Base-emitter saturation voltage	V <sub>BE(SAT)</sub>		-0.96	-1.1	V	I <sub>C</sub> = -3.5A, I <sub>B</sub> = -350mA*
Base-emitter turn-on voltage	V <sub>BE(ON)</sub>		-0.8	-0.9	V	$I_{C} = -3.5A, V_{CE} = -2V *$
Static forward current transfer ratio	h <sub>FE</sub>	300	575			$I_{\rm C}$ = -10mA, $V_{\rm CE}$ = -2V *
		300	450	900		$I_{C} = -1A, V_{CE} = -2V *$
		150	285			$I_{C} = -3.5A, V_{CE} = -2V *$
		10	40			$I_{C}$ = -10A, $V_{CE}$ = -2V *
Transition frequency	f <sub>T</sub>		110			I <sub>C</sub> = -50mA, V <sub>CE</sub> = -10V
						f = 50MHz
Output capacitance	С <sub>ОВО</sub>		45		pF	V <sub>CB</sub> = -10V, f = 1MHz *

## **ELECTRICAL CHARACTERISTICS** (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

#### NOTES

\* Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu s;$  duty cycle  $\leq$  2%.



#### **TYPICAL CHARACTERISTICS**

NOTES:

NOTES:

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Controlling dimensions are in millimeters. Approximate conversions are given in inches

DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.90	1.45	0.035	0.057	E	2.20	3.20	0.0866	0.118
A1	0.00	0.15	0.00	0.006	E1	1.30	1.80	0.0511	0.071
A2	0.90	1.30	0.035	0.051	L	0.10	0.60	0.004	0.024
b	0.20	0.50	0.008	0.020	е	0.95 REF		0.037 REF	
С	0.09	0.26	0.003	0.010	e1	1.90 REF		0.075	5 REF
D	2.70	3.10	0.106	0.122	θ	0°	30°	0°	30°

#### PACKAGE DIMENSIONS

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